

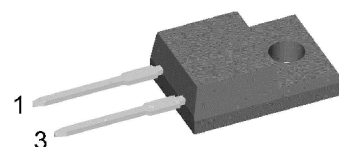
HiPerFRED

V_{RRM}	=	600 V
I_{FAV}	=	15 A
t_{rr}	=	25 ns

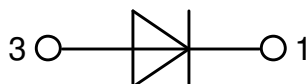
High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Single Diode

Part number

DPG30I600PM



Backside: isolated



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

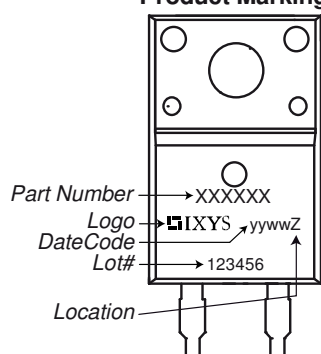
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Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				600	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				600	V
I_R	reverse current, drain current	$V_R = 600\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			250	μA
		$V_R = 600\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			2	mA
V_F	forward voltage drop	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			2,52	V
		$I_F = 60\text{ A}$				3,22	V
		$I_F = 30\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$			1,63	V
		$I_F = 60\text{ A}$				2,27	V
I_{FAV}	average forward current	$T_C = 95^{\circ}\text{C}$ rectangular d = 0.5	$T_{VJ} = 175^{\circ}\text{C}$			15	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^{\circ}\text{C}$		0,84	V
r_F	slope resistance					20	m Ω
R_{thJC}	thermal resistance junction to case					3,5	K/W
R_{thCH}	thermal resistance case to heatsink				0,5		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				165	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_R = 0\text{ V}$		$T_{VJ} = 45^{\circ}\text{C}$		250	A
C_J	junction capacitance	$V_R = 400\text{ V}$ f = 1 MHz		$T_{VJ} = 25^{\circ}\text{C}$	26		pF
I_{RM}	max. reverse recovery current	} $I_F = 30\text{ A}; V_R = 300\text{ V}$ -di _F /dt = 200 A/μs		$T_{VJ} = 25^{\circ}\text{C}$	2,5		A
t_{rr}	reverse recovery time			$T_{VJ} = 100^{\circ}\text{C}$	4,5		A
				$T_{VJ} = 25^{\circ}\text{C}$	25		ns
				$T_{VJ} = 100^{\circ}\text{C}$	70		ns

Package TO-220FP				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal				35	A
T_{VJ}	virtual junction temperature			-55		175	°C
T_{op}	operation temperature			-55		150	°C
T_{stg}	storage temperature			-55		150	°C
Weight					2		g
M_D	mounting torque			0,4		0,6	Nm
F_c	mounting force with clip			20		60	N
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	3,2	2,7			mm
$d_{Spb/Apb}$		terminal to backside	2,5	2,5			mm
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	2500			V
		t = 1 minute		2100			V

Product Marking



Part description

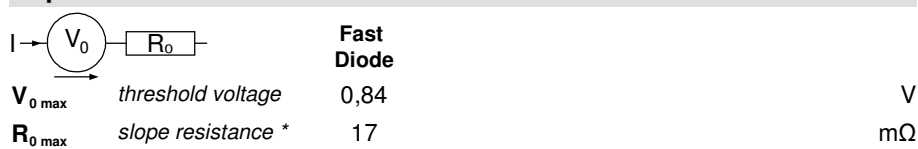
D = Diode
 P = HiPerFRED
 G = extreme fast
 30 = Current Rating [A]
 I = Single Diode
 600 = Reverse Voltage [V]
 PM = TO-220ACFP (2)

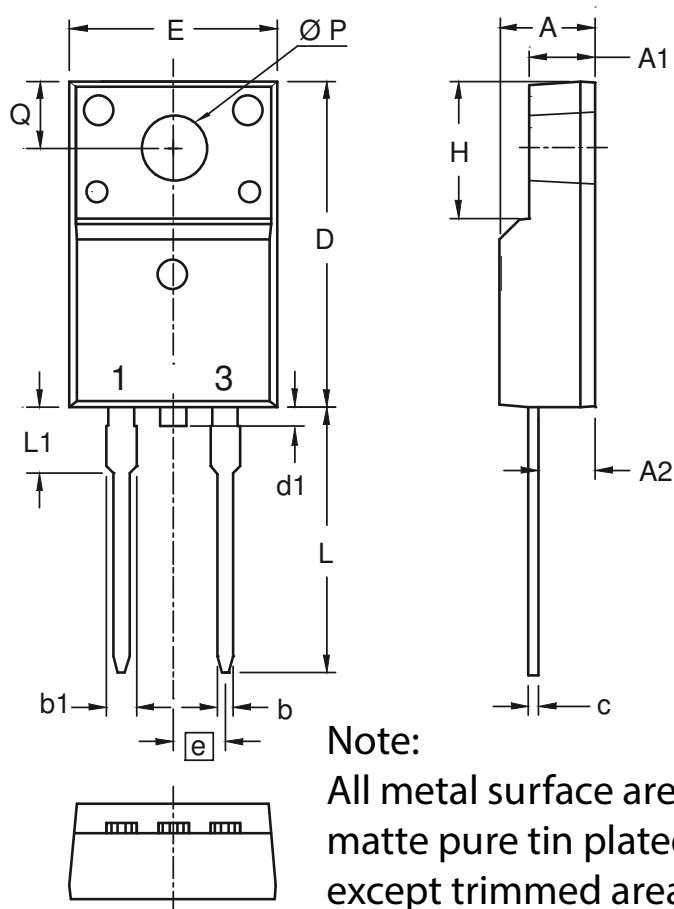
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DPG30I600PM	DPG30I600PM	Tube	50	521763

Equivalent Circuits for Simulation

* on die level

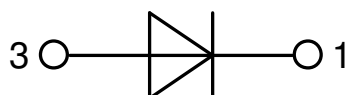
$T_{VJ} = 175^{\circ}\text{C}$



Outlines TO-220FP


Note:
 All metal surface are
 matte pure tin plated
 except trimmed area.

Dim.	Millimeters		Inches	
	min	max	min	max
A	4.50	4.90	0.177	0.193
A1	2.34	2.74	0.092	0.108
A2	2.56	2.96	0.101	0.117
b	0.70	0.90	0.028	0.035
b1	1.27	1.47	0.050	0.058
c	0.45	0.60	0.018	0.024
D	15.67	16.07	0.617	0.633
d1	0	1.10	0	0.043
E	9.96	10.36	0.392	0.408
e	2.54 BSC		0.100 BSC	
H	6.48	6.88	0.255	0.271
L	12.68	13.28	0.499	0.523
L1	3.03	3.43	0.119	0.135
ØP	3.08	3.28	0.121	0.129
Q	3.20	3.40	0.126	0.134



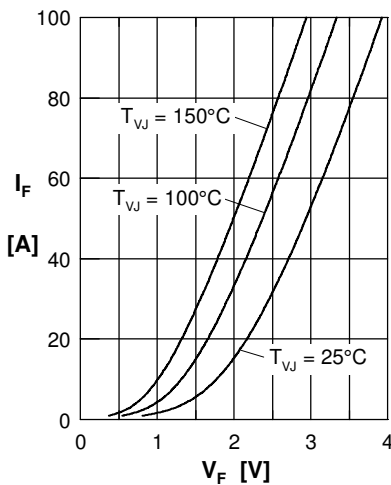
Fast Diode


Fig. 1 Forward current I_F versus V_F

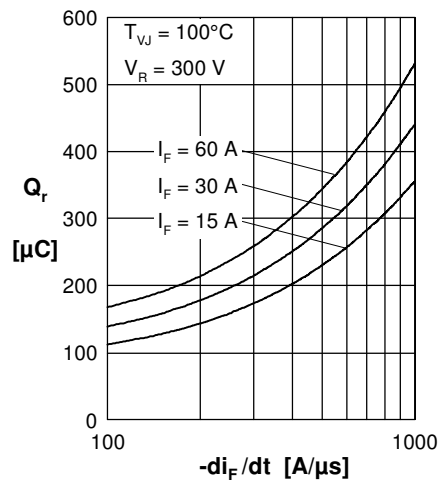


Fig. 2 Typ. reverse recovery charge Q_r versus $-di_F/dt$

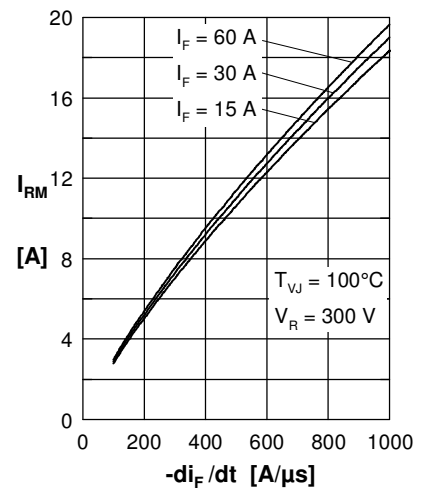


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

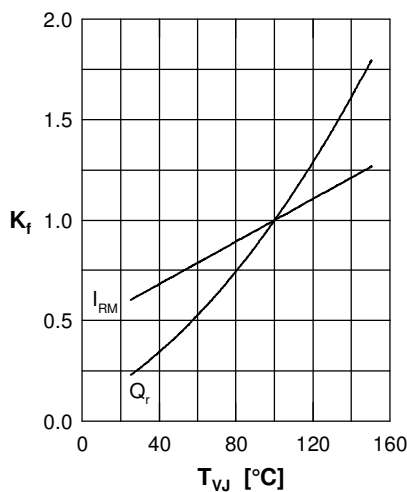


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

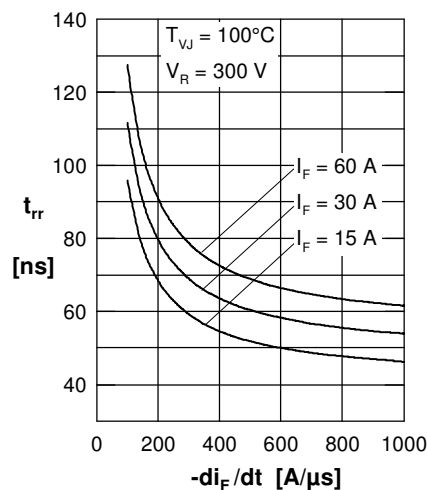


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

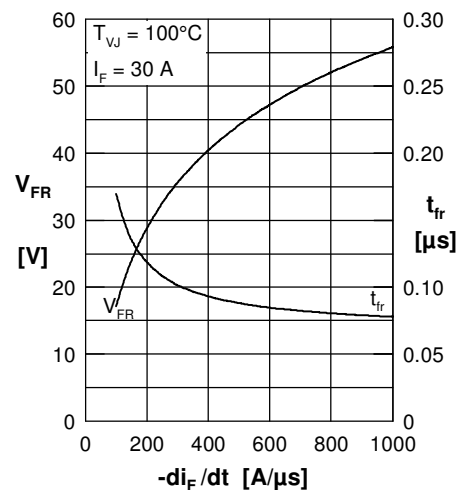


Fig. 6 Typ. peak forward voltage V_{FR} and t_{rr} versus di_F/dt

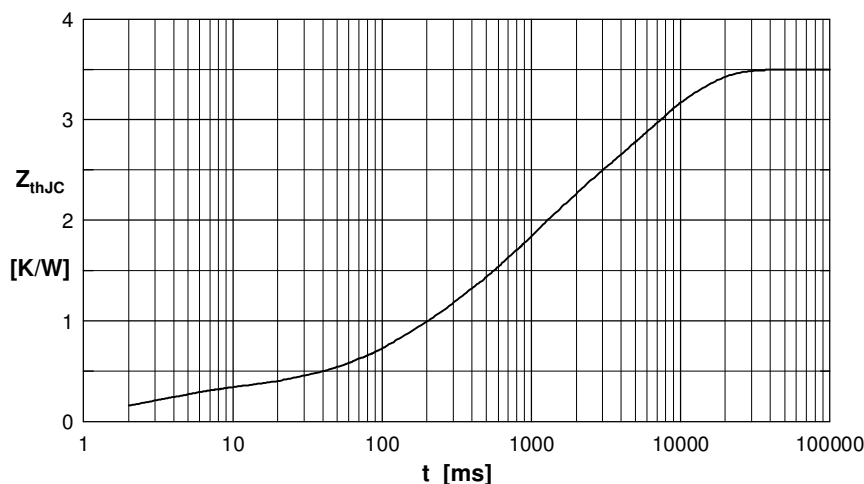


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.30	0.003
2	0.50	0.130
3	1.15	0.800
4	1.55	6.500